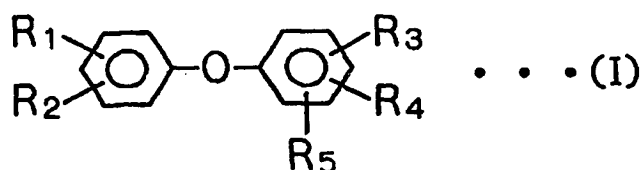


## CLAIMS

1. A developer composition for resists, comprising an organic quaternary ammonium base as a main component,

said developer composition further comprising an anionic surfactant represented by the following general formula (I):



wherein at least one of  $\text{R}_1$  and  $\text{R}_2$  represents an alkyl or alkoxy group having 5 to 18 carbon atoms and the other one represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one of  $\text{R}_3$ ,  $\text{R}_4$  and  $\text{R}_5$  represents an ammonium sulfonate group or a sulfonic acid-substituted ammonium group and the others represent a hydrogen atom, an ammonium sulfonate group or a sulfonic acid-substituted ammonium group, and

$\text{SO}_4^{2-}$ , the content being from 10 to 10,000 ppm.

2. The developer composition for resists according to claim 1, further comprising a lower alcohol, the content being from 0.01 to 5% by mass.

3. The developer composition for resists according to claim 1, further comprising a halogen ion, the content being 1000 ppm or less.

4. A method for formation of a resist pattern, comprising applying a resist composition on

a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to any one of claims 1 to 3 to form a resist pattern.